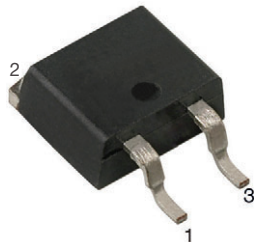
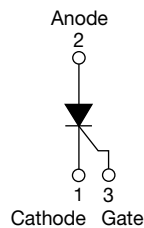


# Thyristor, Surface-Mount, Phase Control SCR, 16 A


**D<sup>2</sup>PAK 2L (TO-263AB 2L)**

**FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**
**LINKS TO ADDITIONAL RESOURCES**


3D Models

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	16 A
$V_{DRM}/V_{RRM}$	1200 V
$V_{TM}$	1.25 V
$I_{GT}$	45 mA
$T_J$	-40 to +125 °C
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)
Circuit configuration	Single SCR

**APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

**DESCRIPTION**

The VS-25TTS12S2LHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

**MECHANICAL DATA**

**Case:** D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	8.5	13.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	16.5	25.0	

**Note**

- $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
$I_{RMS}$		25	
$V_{RRM}/V_{DRM}$		1200	V
$I_{TSM}$		350	A
$V_T$	16 A, $T_J = 25$ °C	1.25	V
dV/dt		500	V/μs
dI/dt		150	A/μs
$T_J$		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM} / I_{DRM}$ , AT 125 °C mA
VS-25TTS12S2LHM3	1200	1200	10



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^\circ\text{C}$ , 180° conduction half sine wave		16		A
Maximum RMS on-state current	$I_{RMS}$			25		
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied		300		
		10 ms sine pulse, no voltage reapplied		350		
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied		450		$A^2s$
		10 ms sine pulse, no voltage reapplied		630		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$ , no voltage reapplied		6300		$A^2\sqrt{s}$
Maximum on-state voltage drop	$V_{TM}$	16 A, $T_J = 25\text{ }^\circ\text{C}$		1.25		V
On-state slope resistance	$r_t$	$T_J = 125\text{ }^\circ\text{C}$		12.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$			1.0		V
Maximum reverse and direct leakage current	$I_{RM} / I_{DM}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	0.5		mA
		$T_J = 125\text{ }^\circ\text{C}$		10		
Holding current	$I_H$	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	-	150	
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		200		
Maximum rate of rise of off-state voltage	$dV/dt$	$T_J = T_J\text{ max.}$ , linear to 80 %, $V_{DRM} = R_g - k = \text{open}$		500		$V/\mu s$
Maximum rate of rise of turned-on current	$di/dt$			150		$A/\mu s$

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	$P_{GM}$			8.0	W
Maximum average gate power	$P_{G(AV)}$			2.0	
Maximum peak positive gate current	$+I_{GM}$			1.5	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$		60	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		45	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		20	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$		2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$		1.0	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{rated value}$		0.25	
Maximum DC gate current not to trigger	$I_{GD}$			2.0	mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^\circ\text{C}$		0.9	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^\circ\text{C}$		4	
Typical turn-off time	$t_q$			110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		-40 to +125	°C
Soldering temperature	$T_S$	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style: 2L D <sup>2</sup> PAK (2L TO-263AB)	25TTS12SH	

**Note**

(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W

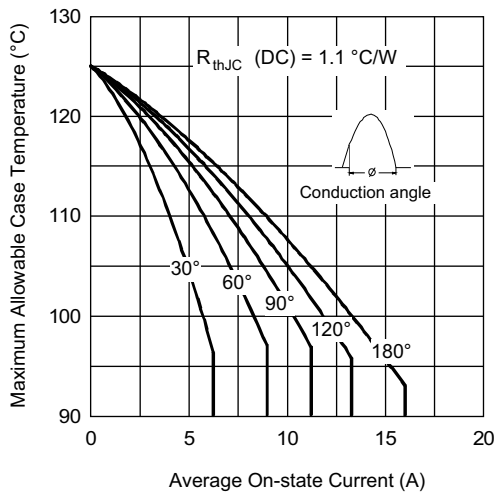


Fig. 1 - Current Rating Characteristics

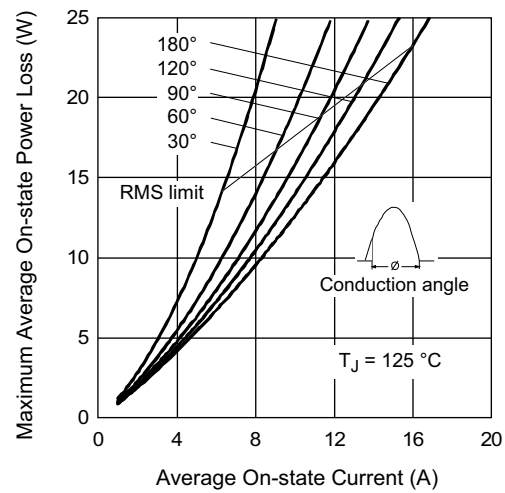


Fig. 3 - On-State Power Loss Characteristics

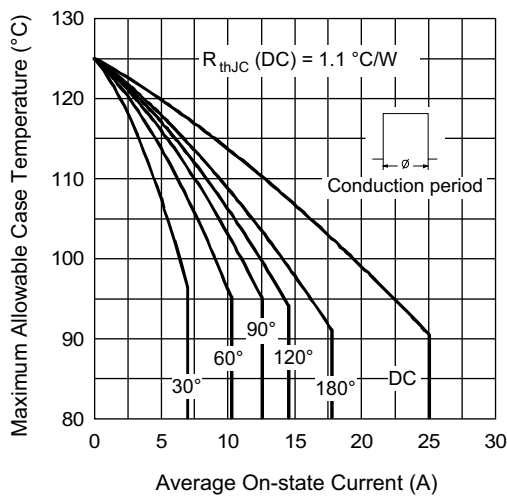


Fig. 2 - Current Rating Characteristics

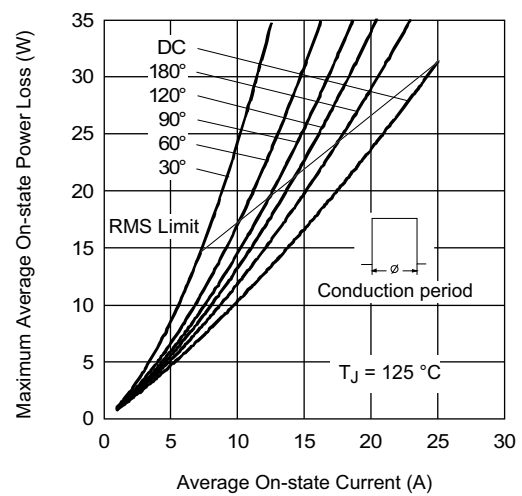


Fig. 4 - On-State Power Loss Characteristics

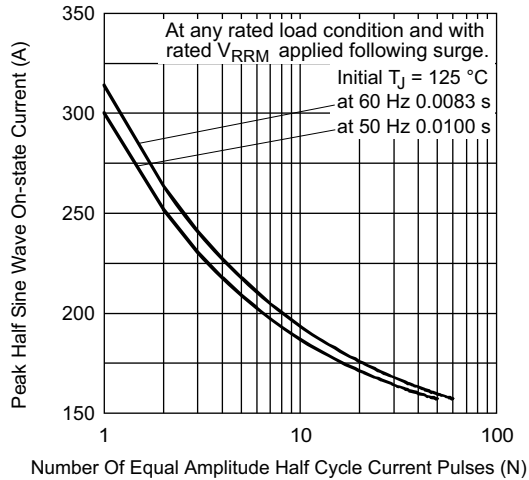


Fig. 5 - Maximum Non-Repetitive Surge Current

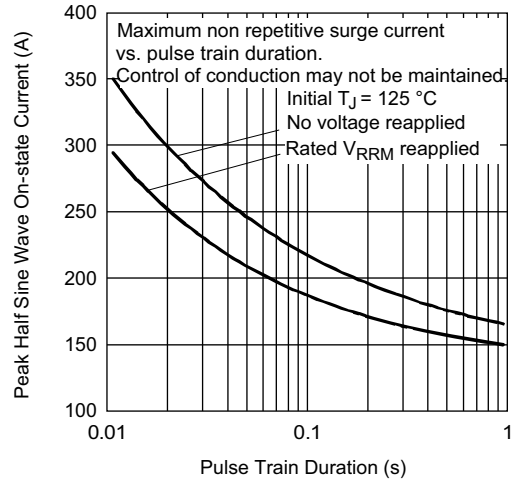


Fig. 6 - Maximum Non-Repetitive Surge Current

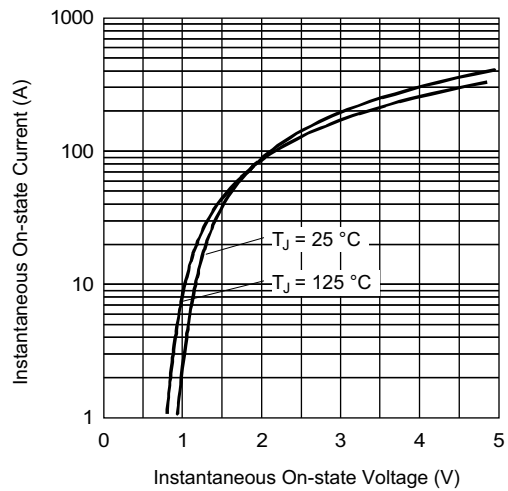


Fig. 7 - On-State Voltage Drop Characteristics

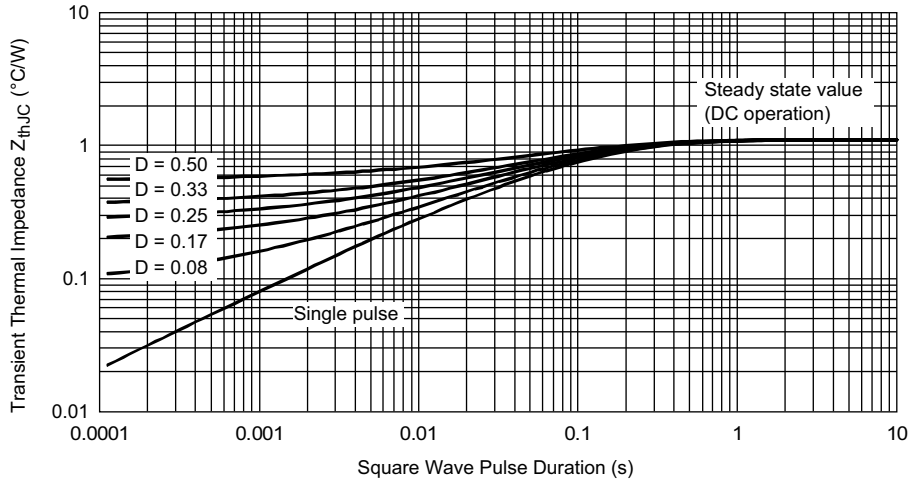


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

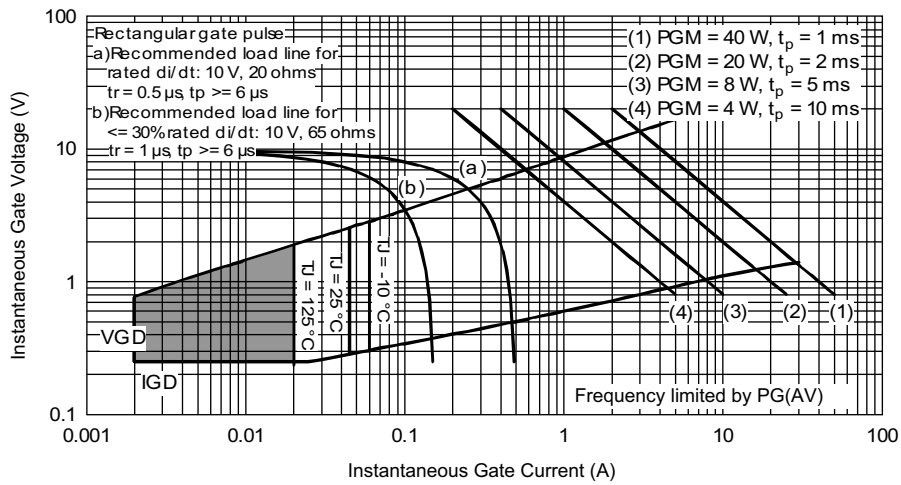
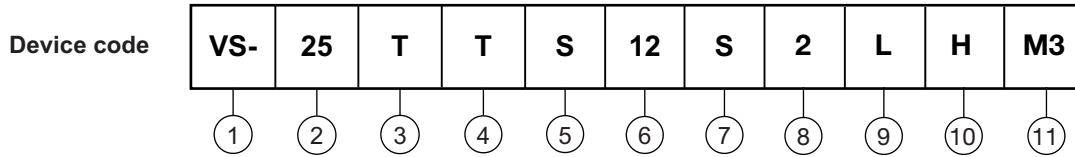


Fig. 9 - Gate Characteristics



## ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Current rating (25 = 25 A)
- 3** - Circuit configuration:  
T = single thyristor
- 4** - Package:  
T = D<sup>2</sup>PAK (TO-263AB)
- 5** - Type of silicon:  
S = standard recovery rectifier
- 6** - Voltage rating: voltage code x 100 = V<sub>RRM</sub> ——— **12 = 1200 V**
- 7** - S = surface mountable
- 8** - 2 = true 2 pin D<sup>2</sup>PAK
- 9** - L = tape and reel (left oriented), for different orientation contact factory
- 10** - H = AEC-Q101 qualified
- 11** - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

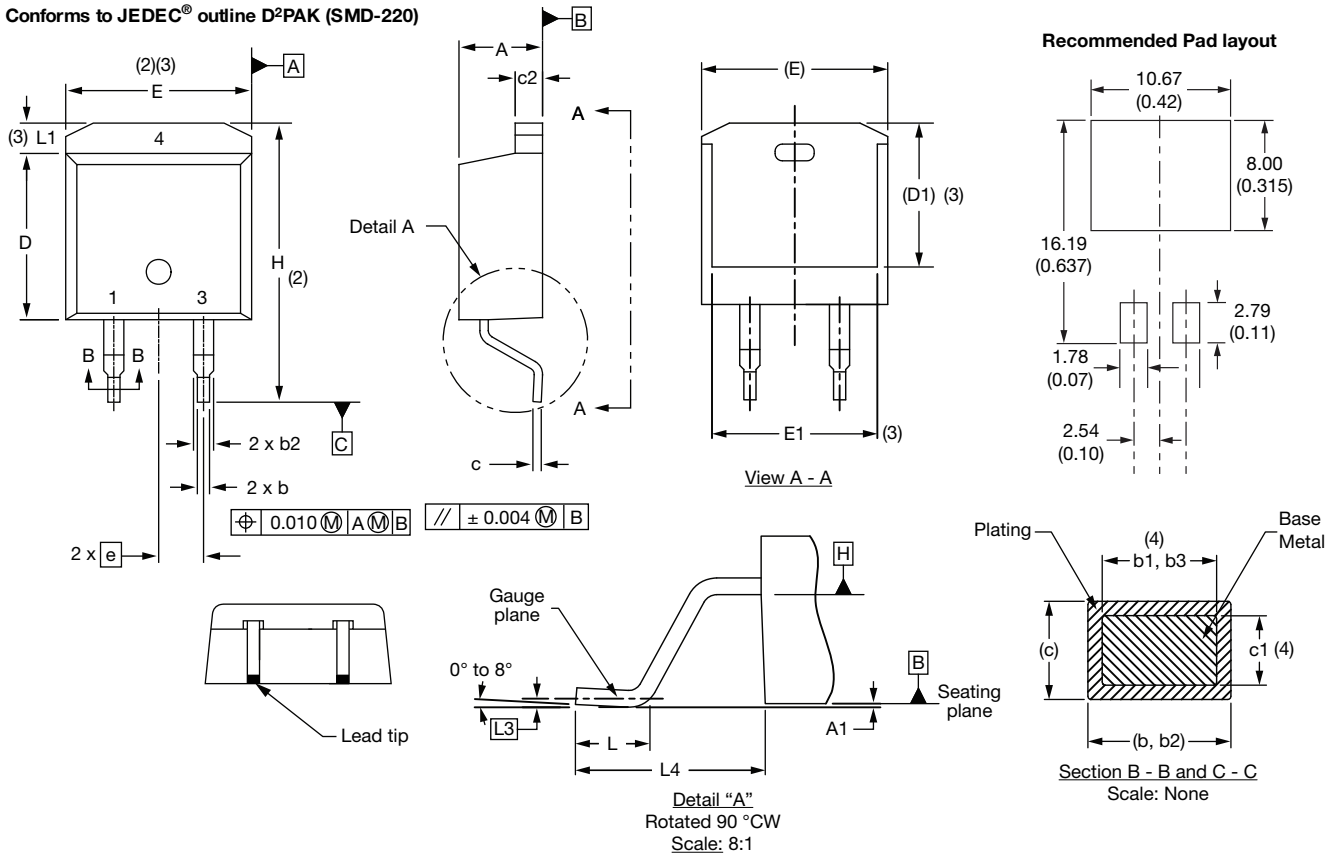
ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-25TTS12S2LHM3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?96683">www.vishay.com/doc?96683</a>
Part marking information	<a href="http://www.vishay.com/doc?96693">www.vishay.com/doc?96693</a>
Packaging information	<a href="http://www.vishay.com/doc?96317">www.vishay.com/doc?96317</a>

### D<sup>2</sup>PAK 2L (TO-263AB 2L)

**DIMENSIONS** in millimeters and inches

Conforms to JEDEC® outline D<sup>2</sup>PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L3	0.25 BSC		0.010 BSC		
c2	1.14	1.65	0.045	0.065		L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2						

**Notes**

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC® outline TO-263AB



## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.